

# Saluru B Krupanidhi

## List of Publications by Year in descending order

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439  
papers

10,839  
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34016

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444  
all docs

444  
docs citations

444  
times ranked

9327  
citing authors

#	ARTICLE	IF	CITATIONS
1	MoS <sub>2</sub> /SnO <sub>2</sub> heterojunction-based self-powered photodetector. Applied Physics Letters, 2022, 120, .	1.5	9
2	Electrically Modulated Wavelength-Selective Photodetection Enabled by $\text{MoS}_2/\text{SnO}_2$ Heterostructure. Physical Review Applied, 2022, 17, .	1.5	11
3	Infrared photodetectors based on multiwalled carbon nanotubes: Insights into the effect of nitrogen doping. Applied Surface Science, 2021, 538, 148187.	3.1	40
4	Enhanced phase transition and infrared photoresponse characteristics in VO <sub>2</sub> (M1) thin films synthesized by DC reactive sputtering on different substrates. Materials Advances, 2021, 2, 3726-3735.	2.6	4
5	Solution-Processed SnSe <sub>2</sub> RGO-Based Bulk Heterojunction for Self-Powered and Broadband Photodetection. ACS Applied Electronic Materials, 2021, 3, 3131-3138.	2.0	12
6	Electrical transport modulation of VO <sub>2</sub> /Si(111) heterojunction by engineering interfacial barrier height. Journal of Applied Physics, 2021, 129, .	1.1	7
7	Overcoming the Challenges Associated with the InN/InGaN Heterostructure via a Nanostructuring Approach for Broad Band Photodetection. ACS Applied Electronic Materials, 2021, 3, 4243-4253.	2.0	4
8	Differentiation of ultraviolet/visible photons from near infrared photons by MoS <sub>2</sub> /GaN/Si-based photodetector. Applied Physics Letters, 2021, 119, .	1.5	19
9	Inhomogeneity-mediated systematic reduction of the Schottky barrier in a Au/GaN nanorod film interface. Semiconductor Science and Technology, 2021, 36, 015017.	1.0	3
10	Defect and strain modulated highly efficient ZnO UV detector: Temperature and low-pressure dependent studies. Applied Surface Science, 2020, 505, 144365.	3.1	46
11	Harvesting energy via stimuli-free water/moisture dissociation by mesoporous SnO <sub>2</sub> -based hydroelectric cell and CuO as a pump for atmospheric moisture. International Journal of Energy Research, 2020, 44, 1276-1283.	2.2	11
12	Temperature-Dependent Electrical Transport and Optoelectronic Properties of SnS <sub>2</sub> /p-Si Heterojunction. ACS Applied Electronic Materials, 2020, 2, 2155-2163.	2.0	23
13	Temperature Dependent S-Shaped Photoluminescence Behavior of InGaN Nanolayers: Optoelectronic Implications in Harsh Environment. ACS Applied Nano Materials, 2020, 3, 8453-8460.	2.4	9
14	Device Architecture for Visible and Near-Infrared Photodetectors Based on Two-Dimensional SnSe <sub>2</sub> and MoS <sub>2</sub> : A Review. Micromachines, 2020, 11, 750.	1.4	19
15	Self-powered, ultrasensitive, room temperature humidity sensors using SnS <sub>2</sub> nanofilms. Scientific Reports, 2020, 10, 14611.	1.6	20
16	Defect-Mediated Transport in Self-Powered, Broadband, and Ultrafast Photoresponse of a MoS <sub>2</sub> /AlN/Si-Based Photodetector. ACS Applied Electronic Materials, 2020, 2, 944-953.	2.0	40
17	Iron-Based Mixed Phosphate Na <sub>4</sub> Fe <sub>3</sub> (PO <sub>4</sub> ) <sub>2</sub> P <sub>2</sub> O <sub>7</sub> Thin Films for Sodium-Ion Microbatteries. ACS Omega, 2020, 5, 7219-7224.	1.6	19
18	Different types of band alignment at MoS <sub>2</sub> /(Al, Ga, In)N heterointerfaces. Applied Physics Letters, 2020, 116, .	1.5	16

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19	Highly Responsive, Self-Powered <i>a</i> -GaN Based UV-A Photodetectors Driven by Unintentional Asymmetrical Electrodes. ACS Applied Electronic Materials, 2020, 2, 769-779.	2.0	31
20	Next-generation self-powered and ultrafast photodetectors based on III-nitride hybrid structures. APL Materials, 2020, 8, .	2.2	30
21	Highly photoresponsive VO <sub>2</sub> (M1) thin films synthesized by DC reactive sputtering. Journal of Materials Science: Materials in Electronics, 2020, 31, 4687-4695.	1.1	16
22	Enhanced humidity responsive ultrasonically nebulised V <sub>2</sub> O <sub>5</sub> thin films. Nano Express, 2020, 1, 010005.	1.2	13
23	Fabrication of smooth thin film of vanadium oxides ( $\text{VO}_x$ ) using pulsed laser deposition. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	8
24	Fabrication of thin film electrode material by pulsed laser deposition. AIP Conference Proceedings, 2019, , .	0.3	0
25	Double Gaussian distribution of barrier heights and self-powered infrared photoresponse of InN/AlN/Si (111) heterostructure. Journal of Applied Physics, 2019, 126, .	1.1	19
26	NO <sub>2</sub> gas sensing performance enhancement based on reduced graphene oxide decorated V <sub>2</sub> O <sub>5</sub> thin films. Nanotechnology, 2019, 30, 224001.	1.3	25
27	Highly Responsive ZnO/AlN/Si Heterostructure-Based Infrared- and Visible-Blind Ultraviolet Photodetectors With High Rejection Ratio. IEEE Transactions on Electron Devices, 2019, 66, 1345-1352.	1.6	17
28	Photodetection Properties of Nonpolar <i>a</i> -Plane GaN Grown by Three Approaches Using Plasma-Assisted Molecular Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900171.	0.8	17
29	A high-performance hydrogen sensor based on a reverse-biased MoS <sub>2</sub> /GaN heterojunction. Nanotechnology, 2019, 30, 314001.	1.3	42
30	Low-cost VO <sub>2</sub> (M1) thin films synthesized by ultrasonic nebulized spray pyrolysis of an aqueous combustion mixture for IR photodetection. RSC Advances, 2019, 9, 9983-9992.	1.7	24
31	Self-Powered, Broad Band, and Ultrafast InGaN-Based Photodetector. ACS Applied Materials & Interfaces, 2019, 11, 10418-10425.	4.0	61
32	Toward a Fast and Highly Responsive SnSe <sub>2</sub> -Based Photodiode by Exploiting the Mobility of the Counter Semiconductor. ACS Applied Materials & Interfaces, 2019, 11, 6184-6194.	4.0	39
33	Preferentially oriented SrLi <sub>2</sub> Ti <sub>6</sub> O <sub>14</sub> thin film anode for Li-ion micro-batteries fabricated by pulsed laser deposition. Electrochimica Acta, 2018, 269, 212-216.	2.6	6
34	Vis-Near-Infrared Photodetectors Based on Methyl Ammonium Lead Iodide Thin Films by Pulsed Laser Deposition. Journal of Electronic Materials, 2018, 47, 2306-2315.	1.0	4
35	In-Plane Anisotropic Photoconduction in Nonpolar Epitaxial <i>a</i> -Plane GaN. ACS Applied Materials & Interfaces, 2018, 10, 16918-16923.	4.0	33
36	Superior Electrochemical Performance of Amorphous Titanium Niobium Oxide Thin Films for Li-Ion Thin Film Batteries. Journal of the Electrochemical Society, 2018, 165, A764-A772.	1.3	12



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55	Sequential Elemental Dealloying Approach for the Fabrication of Porous Metal Oxides and Chemiresistive Sensors Thereof for Electronic Listening. ACS Applied Materials & Interfaces, 2017, 9, 41428-41434.	4.0	27
56	Effect of Illumination Intensities on the Visible and Infrared Photoresponse of Cu <sub>2</sub> SnS <sub>3</sub> Nanostructures. Journal of Nanoscience and Nanotechnology, 2017, 17, 413-419.	0.9	5
57	Mechanistic view on efficient photodetection by solvothermally reduced graphene oxide. Journal of Materials Science: Materials in Electronics, 2017, 28, 14818-14826.	1.1	9
58	Experimental evidence on RH-dependent crossover from an electronic to protonic conduction with an oscillatory behaviour. Applied Physics Letters, 2017, 110, .	1.5	15
59	Na <sub>2</sub> Ti <sub>6</sub> O <sub>13</sub> thin films as anode for thin film sodium ion batteries. AIP Conference Proceedings, 2017, , .	0.3	2
60	Enhanced UV Photodetector Response of ZnO/Si With AlN Buffer Layer. IEEE Transactions on Electron Devices, 2017, 64, 4161-4166.	1.6	25
61	Deep UV-Vis photodetector based on ferroelectric/semiconductor heterojunction. Journal of Applied Physics, 2017, 122, .	1.1	19
62	Solution-Cast Photoconductive Photodetectors Based on CuInSe <sub>2</sub> Nanoparticles. Journal of Nanoscience and Nanotechnology, 2017, 17, 1538-1542.	0.9	5
63	Role of component layers in designing carbon nanotubes-based tandem absorber on metal substrates for solar thermal applications. Solar Energy Materials and Solar Cells, 2016, 155, 397-404.	3.0	8
64	Solution processed Cu <sub>2</sub> SnS <sub>3</sub> thin films for visible and infrared photodetector applications. AIP Advances, 2016, 6, .	0.6	48
65	Cu <sub>2</sub> SnS <sub>3</sub> nanostructures for inorganic-organic hybrid infrared photodetector applications. Materials Research Express, 2016, 3, 105006.	0.8	9
66	Controlled growth of high-quality graphene using hot-filament chemical vapor deposition. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	8
67	Understanding Pt-ZnO:In Schottky nanocontacts by conductive atomic force microscopy. Materials Research Express, 2016, 3, 045023.	0.8	4
68	Fabrication of TiNb <sub>2</sub> O <sub>7</sub> thin film electrodes for Li-ion micro-batteries by pulsed laser deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2016, 213, 90-97.	1.7	27
69	InN Quantum Dot Based Infra-Red Photodetectors. Journal of Nanoscience and Nanotechnology, 2016, 16, 709-714.	0.9	11
70	Structural and optical characterization of nonpolar (10 <sup>-10</sup> ) m-InN/m-GaN epilayers grown by PAMBE. Journal of Crystal Growth, 2016, 433, 74-79.	0.7	5
71	Cu <sub>2</sub> SnS <sub>3</sub> Inorganic-Organic Hybrid Structures for Photovoltaic Applications. Materials Research Society Symposia Proceedings, 2015, 1784, 1.	0.1	1
72	Determination of band offsets at the Al:ZnO/Cu <sub>2</sub> SnS <sub>3</sub> interface using X-ray photoelectron spectroscopy. AIP Advances, 2015, 5, .	0.6	9

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73	Enhanced UV detection by non-polar epitaxial GaN films. AIP Advances, 2015, 5, .	0.6	31
74	Temperature dependent electrical characterisation of Pt/HfO <sub>2</sub> /n-GaN metal-insulator-semiconductor (MIS) Schottky diodes. AIP Advances, 2015, 5, .	0.6	54
75	Impact of Nitridation on Structural and Optical Properties of Epitaxial GaN Films Grown on M-Plane Sapphire by PAMBE. Materials Research Society Symposia Proceedings, 2015, 1736, 76.	0.1	1
76	Nanocomposite Based Organic-Inorganic Cu <sub>3</sub> BiS <sub>3</sub> High Sensitive Hybrid Photonic Devices. Journal of Nanoscience and Nanotechnology, 2015, 15, 2742-2752.	0.9	7
77	Study of band offsets at the Cu <sub>2</sub> SnS <sub>3</sub> /In <sub>2</sub> O <sub>3</sub> : Sn interface using x-ray photoelectron spectroscopy. Materials Research Express, 2015, 2, 065901.	0.8	4
78	Solution processible Cu <sub>2</sub> SnS <sub>3</sub> thin films for cost effective photovoltaics: Characterization. Materials Chemistry and Physics, 2015, 167, 309-314.	2.0	24
79	Observation of Room Temperature Ferromagnetism in InN Nanostructures. Journal of Nanoscience and Nanotechnology, 2015, 15, 4426-4430.	0.9	7
80	Transport properties of solution processed Cu <sub>2</sub> SnS <sub>3</sub> /AZnO heterostructure for low cost photovoltaics. Solar Energy Materials and Solar Cells, 2015, 143, 152-158.	3.0	38
81	Preferential polarization and its reversal in polycrystalline BiFeO <sub>3</sub> /La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> heterostructures. Solid State Communications, 2015, 208, 15-20.	0.9	4
82	Growth and electrical transport properties of InGaN/GaN heterostructures grown by PAMBE. Materials Research Bulletin, 2015, 61, 539-543.	2.7	9
83	High indium non-polar InGaN clusters with infrared sensitivity grown by PAMBE. AIP Advances, 2015, 5, 037112.	0.6	8
84	Binary group III-nitride based heterostructures: band offsets and transport properties. Journal Physics D: Applied Physics, 2015, 48, 423001.	1.3	62
85	Trap modulated photoresponse of InGaN/Si isotype heterojunction at zero-bias. Journal of Applied Physics, 2015, 118, .	1.1	19
86	Barrier height inhomogeneity in electrical transport characteristics of InGaN/GaN heterostructure interfaces. AIP Advances, 2015, 5, .	0.6	16
87	An insight to the low temperature conduction mechanism of c-axis grown Al-doped ZnO, a widely used transparent conducting oxide. Journal Physics D: Applied Physics, 2015, 48, 015301.	1.3	10
88	CuIn <sub>1-x</sub> Al <sub>x</sub> Se <sub>2</sub> Thin Films Grown by Co-Sputtering and Modified Selenization: Application in Flexible Solar Cells. IEEE Journal of the Electron Devices Society, 2015, 3, 244-253.	1.2	2
89	Plasmonic enhancement of photocurrent in GaN based UV photodetectors. , 2014, , .		9
90	Semipolar and nonpolar GaN epi-films grown on m-sapphire by plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2014, 116, .	1.1	38

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91	Near-infrared photoactive Cu <sub>3</sub> BiS <sub>3</sub> thin films by co-evaporation. Journal of Applied Physics, 2014, 115, .	1.1	25
92	Growth and Characterization of a-plane In <sub>0.2</sub> Ga <sub>0.8</sub> N/ GaN hetrostructures on r-Sapphire. Materials Research Society Symposia Proceedings, 2014, 1736, 31.	0.1	0
93	Pt/n-GaN metal-semiconductor and Pt/HfO <sub>2</sub> /n-GaN metal-insulator-semiconductor Schottky diodes. Materials Research Society Symposia Proceedings, 2014, 1736, 7.	0.1	0
94	Smart Materials for Energy Harvesting, Energy Storage, and Energy Efficient Solid-State Electronic Refrigeration. Springer Tracts in Mechanical Engineering, 2014, , 303-315.	0.1	1
95	Study of InN nanorods growth mechanism using ultrathin Au layer by plasma-assisted MBE on Si(111). Applied Nanoscience (Switzerland), 2014, 4, 121-125.	1.6	2
96	Temperature dependent electrical behaviour of Cu <sub>2</sub> SnS <sub>3</sub> films. AIP Advances, 2014, 4, 037121.	0.6	10
97	Transport properties of CuIn <sub>1-x</sub> Al <sub>x</sub> Se <sub>2</sub> /AZnO heterostructure for low cost thin film photovoltaics. Dalton Transactions, 2014, 43, 1974-1983.	1.6	29
98	Effects of growth temperature on nonpolar a-plane InN grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 932-935.	0.8	3
99	Fabrication of large-area PbSe films at the organic-aqueous interface and their near-infrared photoresponse. Journal of Materials Chemistry C, 2014, 2, 6283.	2.7	10
100	Carbon Nanotube-Based Tandem Absorber with Tunable Spectral Selectivity: Transition from Near-Perfect Blackbody Absorber to Solar Selective Absorber. Advanced Materials, 2014, 26, 2552-2557.	11.1	95
101	Solution Processed Cu <sub>2</sub> CoSn <sub>4</sub> Thin Films for Photovoltaic Applications. Crystal Growth and Design, 2014, 14, 3685-3691.	1.4	63
102	Double Gaussian distribution of barrier height observed in densely packed GaN nanorods over Si (111) heterostructures. Journal of Applied Physics, 2014, 116, .	1.1	8
103	Impact of substrate nitridation on the photoluminescence and photovoltaic characteristics of GaN grown on p-Si (100) by molecular beam epitaxy. Journal of Materials Science: Materials in Electronics, 2013, 24, 3371-3375.	1.1	1
104	Anomalous magnetic behavior of La <sub>0.6</sub> Sr <sub>0.4</sub> MnO <sub>3</sub> nano-tubes constituted with 3-12 nm particles. Applied Physics A: Materials Science and Processing, 2013, 111, 605-612.	1.1	15
105	Facile synthesis of Cu <sub>2</sub> CoSn <sub>4</sub> nanoparticles exhibiting red-edge-effect: Application in hybrid photonic devices. Journal of Applied Physics, 2013, 114, .	1.1	61
106	Near infrared detectors based on HgSe and HgCdSe quantum dots generated at the liquid-liquid interface. Journal of Materials Chemistry C, 2013, 1, 6184.	2.7	36
107	Substrate impact on the growth of InN nanostructures by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 409-412.	0.8	4
108	Low dimensional fabrication of giant dielectric CaCu <sub>3</sub> Ti <sub>4</sub> O <sub>12</sub> through soft e-beam lithography. Journal of Alloys and Compounds, 2013, 547, 147-151.	2.8	14



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109	Electrical transport studies of MBE grown InGaN/Si isotype heterojunctions. Current Applied Physics, 2013, 13, 26-30.	1.1	13
110	Spectroscopic Studies of In <sub>2</sub> O <sub>3</sub> Nanostructures; Photovoltaic Demonstration of In <sub>2</sub> O <sub>3</sub> /p-Si Heterojunction. Journal of Nanoscience and Nanotechnology, 2013, 13, 498-503.	0.9	4
111	Sol-gel processed Cu <sub>2</sub> SnS <sub>3</sub> films for photovoltaics. , 2013, , .		1
112	Electrical and Optical Properties of Electron Irradiated ZnO: Li Thin Films. Advanced Materials Research, 2013, 699, 257-261.	0.3	1
113	Molecular beam epitaxial growth of (1 1 -2 2) GaN on m-plane sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 381-384.	0.8	1
114	CuIn <sub>1-x</sub> Al <sub>x</sub> Se <sub>2</sub> ; solar cells fabricated on the flexible substrates by co-sputtering and modified selenization. , 2013, , .		0
115	Electrocaloric Effect in 0.85PMN-0.15PT Thin Films Deposited by Pulsed Laser Deposition. Ferroelectrics, 2013, 453, 38-43.	0.3	3
116	Near-infrared photoactive Cu <sub>2</sub> ZnSnS <sub>4</sub> thin films by co-sputtering. AIP Advances, 2013, 3, .	0.6	32
117	Tailoring the Cu(In, Al)S <sub>2</sub> nanostructures for photonic applications. , 2013, , .		3
118	Tailoring the Band Gap and Transport Properties of Cu <sub>3</sub> BiS <sub>3</sub> Nanopowders for Photodetector Applications. Journal of Nanoscience and Nanotechnology, 2013, 13, 3901-3909.	0.9	13
119	Comparative studies on photovoltaic performance of InN nanostructures/p-Si(100) heterojunction devices grown by molecular beam epitaxy. Materials Research Society Symposia Proceedings, 2012, 1391, 95.	0.1	1
120	Molecular Beam Epitaxial Growth of Nonpolar a-plane InN/ GaN Heterostructures. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
121	Growth and study of CuIn <sub>1-x</sub> Al <sub>x</sub> Se <sub>2</sub> thin films for photovoltaic applications. , 2012, , .		0
122	Current transport in nonpolar a-plane InN/GaN heterostructures Schottky junction. Journal of Applied Physics, 2012, 112, 023706.	1.1	15
123	Unusual photoresponse of indium doped ZnO/organic thin film heterojunction. Applied Physics Letters, 2012, 100, .	1.5	62
124	Structural Characterization and Ultraviolet Photoresponse of GaN Nanodots Grown by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 085202.	1.1	10
125	Studies on Field Dependent Domain Structures in Multi-Grained 0.85PbMg <sub>1/3</sub> Nb <sub>2/3</sub> O <sub>3</sub> ∕0.15PbTiO <sub>3</sub> Thin Films by Scanning Force Microscopy. Integrated Ferroelectrics, 2012, 134, 39-47.	0.3	1
126	Band-Structure Lineup at In <sub>0.2</sub> Ga <sub>0.8</sub> N/Si Heterostructures by X-ray Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2012, 51, 020203.	0.8	2



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127	Tuning the photoluminescence of ZnO thin films by indium doping. , 2012, , .		0
128	Growth and properties of nonpolar a-plane GaN grown on r-sapphire by plasma assisted molecular beam epitaxy. Proceedings of SPIE, 2012, , .	0.8	0
129	Wurtzite InN nanodots on Si(100) by molecular beam epitaxy. Proceedings of SPIE, 2012, , .	0.8	0
130	Solution-based synthesis of cobalt-doped ZnO thin films. Thin Solid Films, 2012, 524, 137-143.	0.8	45
131	Effect of carrier concentration of InN on the transport behavior of InN/GaN heterostructure based Schottky junctions. Solid State Communications, 2012, 152, 1771-1775.	0.9	2
132	Indium flux, growth temperature and RF power induced effects in InN layers grown on GaN/Si substrate by plasma-assisted MBE. Journal of Alloys and Compounds, 2012, 513, 6-9.	2.8	9
133	Cobalt-doped ZnO nanowires on quartz: Synthesis by simple chemical method and characterization. Journal of Crystal Growth, 2012, 343, 7-12.	0.7	30
134	Influence of GaN underlayer thickness on structural, electrical and optical properties of InN films grown by PAMBE. Journal of Crystal Growth, 2012, 354, 208-211.	0.7	10
135	Large nonlinear refraction and two photon absorption in ferroelectric Bi <sub>2</sub> VO <sub>5.5</sub> thin films. Optical Materials, 2012, 34, 1822-1825.	1.7	9
136	Synthesis and structural characterization of two-dimensional hierarchical covellite nano-structures. Materials Chemistry and Physics, 2012, 137, 466-471.	2.0	17
137	Perovskite phase transformation in 0.65Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> -0.35PbTiO <sub>3</sub> nanoparticles derived by sol-gel. Journal of Applied Physics, 2012, 111, 024314.	1.1	4
138	Gallium and indium co-doped ZnO thin films for white light emitting diodes. Physica Status Solidi - Rapid Research Letters, 2012, 6, 34-36.	1.2	20
139	Determination of MBE grown wurtzite GaN/Ge <sub>3</sub> N <sub>4</sub> /Ge heterojunctions band offset by X-ray photoelectron spectroscopy. Physica Status Solidi (B): Basic Research, 2012, 249, 58-61.	0.7	19
140	Carrier transport studies of In <sub>3</sub> N <sub>4</sub> /Si <sub>3</sub> N <sub>4</sub> /Si isotype heterojunctions. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 994-997.	0.8	9
141	Analysis of the temperature-dependent current-voltage characteristics and the barrier-height inhomogeneities of Au/GaN Schottky diodes. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1575-1578.	0.8	12
142	Novel Radiation-Induced Properties of Graphene and Related Materials. Macromolecular Chemistry and Physics, 2012, 213, 1146-1163.	1.1	67
143	Carrier concentration dependence of donor activation energy in n-type GaN epilayers grown on Si (111) by plasma-assisted MBE. Materials Research Bulletin, 2012, 47, 1306-1309.	2.7	11
144	Valence band offset at GaN/Î <sup>2</sup> -Si <sub>3</sub> N <sub>4</sub> and Î <sup>2</sup> -Si <sub>3</sub> N <sub>4</sub> /Si(111) heterojunctions formed by plasma-assisted molecular beam epitaxy. Thin Solid Films, 2012, 520, 4911-4915.	0.8	13

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145	Study of n-ZnO/p-Si (100) thin film heterojunctions by pulsed laser deposition without buffer layer. Thin Solid Films, 2012, 520, 5894-5899.	0.8	64
146	Solvothermal Synthesis, Structural and Optical Properties of Phase-Pure Cu <sub>3</sub> BiS <sub>3</sub> Nano-Powders Exhibiting Near-IR Photodetection. Advanced Science, Engineering and Medicine, 2012, 4, 89-95.	0.3	3
147	Band-Structure Lineup at In <sub>0.2</sub> Ga <sub>0.8</sub> N/Si Heterostructures by X-ray Photoelectron Spectroscopy. Japanese Journal of Applied Physics, 2012, 51, 020203.	0.8	1
148	Solution processed reduced graphene oxide ultraviolet detector. Applied Physics Letters, 2011, 99, .	1.5	101
149	Substrate nitridation induced modulations in transport properties of wurtzite GaN/p-Si (100) heterojunctions grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	21
150	Experimental evidence of Ga-vacancy induced room temperature ferromagnetic behavior in GaN films. Applied Physics Letters, 2011, 99, 162512.	1.5	45
151	Size dependent bandgap of molecular beam epitaxy grown InN quantum dots measured by scanning tunneling spectroscopy. Journal of Applied Physics, 2011, 110, 114317.	1.1	9
152	An aqueous-solution based low-temperature pathway to synthesize giant dielectric CaCu <sub>3</sub> Ti <sub>4</sub> O <sub>12</sub> Highly porous ceramic matrix and submicron sized powder. Journal of Alloys and Compounds, 2011, 509, 4381-4385.	2.8	20
153	Structural and dielectric behavior of pulsed laser ablated Sr <sub>0.6</sub> Ca <sub>0.4</sub> TiO <sub>3</sub> thin film and asymmetric multilayer of SrTiO <sub>3</sub> and CaTiO <sub>3</sub> . Journal of Crystal Growth, 2011, 337, 7-12.	0.7	3
154	Indium Nitride (InN) Nanostructures Grown by Plasma-Assisted Molecular Beam Epitaxy (PAMBE). , 2011, , .		0
155	Effect of N/Ga flux ratio on transport behavior of Pt/GaN Schottky diodes. Journal of Applied Physics, 2011, 110, .	1.1	8
156	Barrier height inhomogeneities in InN/GaN heterostructure based Schottky junctions. Solid State Communications, 2011, 151, 1420-1423.	0.9	15
157	Structural and optical properties of nonpolar (11 $\bar{2}$ 0) a-plane GaN grown on (1 $\bar{1}$ 02) r-plane sapphire substrate by plasma-assisted molecular beam epitaxy. Scripta Materialia, 2011, 65, 33-36.	2.6	15
158	Synthesis, structural characterization and ferroelectric properties of Pb <sub>0.76</sub> Ca <sub>0.24</sub> TiO <sub>3</sub> nanotubes. Materials Chemistry and Physics, 2011, 131, 443-448.	2.0	5
159	Growth of InN layers on Si (111) using ultra thin silicon nitride buffer layer by NPA-MBE. Materials Letters, 2011, 65, 1396-1399.	1.3	20
160	Structural and electrical studies on Bi <sub>2</sub> VO <sub>5.5</sub> /Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> multilayer thin films. Journal of Materials Science: Materials in Electronics, 2011, 22, 639-648.	1.1	3
161	Kinetics of self-assembled InN quantum dots grown on Si (111) by plasma-assisted MBE. Journal of Nanoparticle Research, 2011, 13, 1281-1287.	0.8	11
162	Reduction of oxygen impurity at GaN/ $\bar{1}$ <sup>2</sup> -Si <sub>3</sub> N <sub>4</sub> /Si interface via SiO <sub>2</sub> to Ga <sub>2</sub> O conversion by exposing of Si surface under Ga flux. Journal of Crystal Growth, 2011, 327, 272-275.	0.7	4

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